

PCN Number:	20130715001		PCN Date:	07/25/2013	
Title:	Qualification of MIHO 8 - Dallas Bump – Carsem Suzhou (CSZ) as additional Fab site and Assembly site options for TPS22965xxx devices				
Customer Contact:	PCN Manager	Phone:	+1(214)480-6037	Dept:	Quality Services
*Proposed 1st Ship Date:	10/25/2013	Estimated Sample Availability:	Date provided at sample request.		
Change Type:					
<input checked="" type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process	<input checked="" type="checkbox"/>	Assembly Materials
<input type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification	<input type="checkbox"/>	Mechanical Specification
<input checked="" type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process
<input checked="" type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material	<input type="checkbox"/>	Wafer Bump Process
<input checked="" type="checkbox"/>	Wafer Fab Site	<input checked="" type="checkbox"/>	Wafer Fab Materials	<input type="checkbox"/>	Wafer Fab Process
PCN Details					
Description of Change:					
<p>This notification is to announce the qualification of MIHO 8 as an additional Fab site, Dallas Wafer Bump as an additional Wafer Bump site and Carsem Suzhou (CSZ) as an additional Assembly / Test site option for the TPS22965DSGR and TPS22965DSGT devices. Material differences are shown in the following table:</p>					
		TI CLARK	Carsem Suzhou		
Mold Compound		4208625	G770HCD		
Mount Compound		4207768	6491681		
Bond Wire		1.98 Mil Dia., Cu	2.0mil Diameter, Cu		
Leadframe (Finish, Base)		NiPdAu	NiPdAu		
<p>Wafer Diameter change is shown below:</p>					
Currently Qualified Site, Process, Wafer Dia.		Additional Site, Process, Wafer Dia.			
RFAB, LBC7 Process, 300mm		MIHO8, LBC7 Process, 200mm			
<p>Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ.</p>					
Reason for Change:					
Continuity of Supply					
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):					
None					

Changes to product identification resulting from this PCN:

Shipment Labels:

Current

Chip Site	Chip site code (20L)	Chip country code (21L)
RFAB	RFB	USA

New

Chip Site	Chip site code (20L)	Chip country code (21L)
MIH08	MH8	JPN

Current

Assembly Site	Assembly site Origin (22L)	Assembly country Origin (23L)
TI CLARK - Philippines	QAB	PHL

New

Assembly Site	Assembly site Origin (22L)	Assembly country Origin (23L)
Carsem Suzhou	CSZ	CHN

Device Marking for TI Clark and Carsem Suzhou are the same.

Assembly site code for TI Clark = I

Assembly site code for Carsem Suzhou = F

Sample product shipping label (not actual product label)

Product Affected:

TPS22965DSGR	TPS22965DSGT
--------------	--------------

Qualification Data: (Approved: 7/11/2013)

This qualification has been developed for the validation of this change. The qualification data will validate that the proposed change meets the applicable released technical specifications.

Qualification Device: TPS22965DSGR

Wafer Fab Site:	MIHO 8	Assembly Site:	Carsem Suzhou
Wafer Fab Process:	LBC7	# Pins-Designator:	8-DSG
Wafer diameter:	200mm	Package Family:	DSG
Metallization:	TiN/AICu.5/TiN	Lead Frame (Finish, Base):	NiPdAu, Cu
Passivation:	PECVDOX/NITRIDE	Bond Wire:	2.0 Mil Dia., Cu

Qualification: **Plan** **Test Results**

Reliability Test	Conditions	Sample Size /Fail
Electrical Characterization – Limit Verification	Per datasheet spec	Pass
ESD HBM	1000V	3/0
ESD CDM	250V	3/0
Physical Dimensions	Per mechanical drawing	5/0
Bond Strength	76 ball bonds	76/0
Die Shear	-	8/0
Latch-up	(per JESD78)	6/0

**Preconditioning: MSL 2@260C

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com